

## PATENT ASSIGNMENT COVER SHEET

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EPAS ID: PAT6875349

<b>SUBMISSION TYPE:</b>	NEW ASSIGNMENT
<b>NATURE OF CONVEYANCE:</b>	ASSIGNMENT
<b>CONVEYING PARTY DATA</b>	
<b>Name</b>	<b>Execution Date</b>
JIUN-SHENG YANG	07/27/2021
HSING-HAO CHEN	07/27/2021
<b>RECEIVING PARTY DATA</b>	
<b>Name:</b>	WINBOND ELECTRONICS CORP.
<b>Street Address:</b>	NO. 8 KEYA 1ST RD., DAYA DISTRICT, CENTRAL TAIWAN SCIENCE PARK.
<b>City:</b>	TAICHUNG CITY
<b>State/Country:</b>	TAIWAN
<b>PROPERTY NUMBERS Total: 1</b>	
<b>Property Type</b>	<b>Number</b>
<b>Application Number:</b>	17402087
<b>CORRESPONDENCE DATA</b>	
<b>Fax Number:</b>	(703)621-7155
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>	
<b>Phone:</b>	7036217140
<b>Email:</b>	mailroom@mg-ip.com, ymc@mg-ip.com
<b>Correspondent Name:</b>	MUNCY, GEISSLER, OLDS & LOWE, PC
<b>Address Line 1:</b>	4000 LEGATO RD., SUITE 310
<b>Address Line 4:</b>	FAIRFAX, VIRGINIA 22033
<b>ATTORNEY DOCKET NUMBER:</b>	0941/3971PUS1
<b>NAME OF SUBMITTER:</b>	JOE MCKINNEY MUNCY
<b>SIGNATURE:</b>	/Joe Mckinney Muncy/
<b>DATE SIGNED:</b>	08/20/2021
<b>Total Attachments: 2</b>	
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## ASSIGNMENT

WHEREAS, Jiun-Sheng YANG and Hsing-Hao CHEN

hereafter referred to as ASSIGNOR, has/have invented certain new and useful improvements as described and set forth in the below identified application for United States Letters Patent:

Title: SEMICONDUCTOR MEMORY STRUCTURE AND METHOD FOR FORMING

THE SAME

Filed: 13 August 2021

Serial No. 17402087

Executed on: \_\_\_\_\_

WHEREAS, Winbond Electronics Corp. of No. 8 Keya 1st Rd., Daya District, Central Taiwan Science Park, Taichung City, Taiwan, R.O.C. hereinafter referred to as ASSIGNEE, is desirous of acquiring ASSIGNOR'S interest in the said invention and application and in any U.S. Letters Patent which may be granted on the same;

NOW, THEREFORE, TO ALL WHOM IT MAY CONCERN: Be it known that, for good and valuable consideration, receipt of which is hereby acknowledged by Assignor, Assignor has/have sold, assigned and transferred, and by these presents does/do sell, assign and transfer unto the said Assignee, and Assignee's successors and assigns, all his/her/their rights, title and interest in and to the said invention and application and all future improvements thereon, and in and to any Letters Patent which may hereafter be granted on the same in the United States, and the entire rights, title and interest in and to any and all foreign patents and applications for any invention described in said U.S. patent applications, in any and all countries foreign to the U.S., including all rights of priority arising from them, and all the rights and privileges under any and all forms of protection, including patents, that may be granted in said countries foreign to the U.S. for them, the said interest to be held and enjoyed by said Assignee as fully and exclusively as it would have been held and enjoyed by said Assignor had this Assignment and transfer not been made, to the full end and term of any Letters Patent which may be granted thereon, or of any division, renewal, continuation in whole or in part, substitution, conversion, reissue, prolongation or extension thereof.

Assignor further agrees/agree that he/she/they will, without charge to said Assignee, but at Assignee's expense, cooperate with Assignee in the prosecution of said application and/or applications, execute, verify, acknowledge and deliver all such further papers, including applications for Letters Patent and for the reissue thereof, and instruments of assignment and transfer thereof, and will perform such other acts as Assignee lawfully may request, to obtain or maintain Letters Patent for said invention and improvement, and to vest title thereto in said Assignee, or Assignee's successors and assigns.

IN TESTIMONY WHEREOF, Assignor has/have signed his/her/their name(s) on the date(s) indicated.

July 27, 2021  
Date

Jiun Sheng Yang  
Name: Jiun-Sheng YANG

July 27, 2021  
Date

Hsing Hao CHEN  
Name: Hsing-Hao CHEN

DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION  
USING APPLICATION DATA SHEET (37 CFR 1.76)

Title of the  
Invention:

SEMICONDUCTOR MEMORY STRUCTURE AND METHOD FOR  
FORMING THE SAME

As the below named inventor, I hereby declare that:

This declaration is directed to the attached application, or,  
if the application is not attached hereto, United States application or PCT  
international application number \_\_\_\_\_ filed on  
\_\_\_\_\_.

The above-identified application was made or authorized to be made by me.

I believe that I am the original inventor or an original joint inventor of a  
claimed invention in the application.

I hereby acknowledge that any willful false statement made in this  
declaration is punishable under 18 U.S.C. 1001 by fine or imprisonment of not  
more than five (5) years, or both.

LEGAL NAME OF INVENTOR

Inventor's  
Name⇒

Inventor: Jiun-Sheng YANG

Date: July 27, 2021

Inventor's  
Signature⇒

Signature:

*Jiun Sheng Yang*

Additional inventors are being named on the 1 supplemental  
sheet(s) attached hereto.